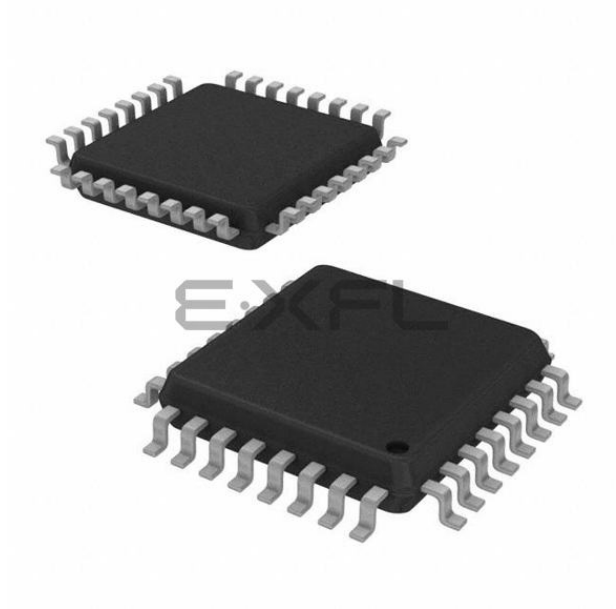

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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	32MHz
Connectivity	I²C, IrDA, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, POR, PWM, WDT
Number of I/O	27
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	2K x 8
RAM Size	8K x 8
Voltage - Supply (Vcc/Vdd)	1.65V ~ 3.6V
Data Converters	A/D 10x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	32-LQFP
Supplier Device Package	32-LQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l051k8t7

List of tables

3.8 Memories

The STM32L051x6/8 devices have the following features:

- 8 Kbytes of embedded SRAM accessed (read/write) at CPU clock speed with 0 wait states. With the enhanced bus matrix, operating the RAM does not lead to any performance penalty during accesses to the system bus (AHB and APB buses).
- The non-volatile memory is divided into three arrays:
  - 32 or 64 Kbytes of embedded Flash program memory
  - 2 Kbytes of data EEPROM
  - Information block containing 32 user and factory options bytes plus 4 Kbytes of system memory

The user options bytes are used to write-protect or read-out protect the memory (with 4 Kbyte granularity) and/or readout-protect the whole memory with the following options:

- **Level 0**: no protection
- **Level 1**: memory readout protected.

  The Flash memory cannot be read from or written to if either debug features are connected or boot in RAM is selected
- **Level 2**: chip readout protected, debug features (Cortex-M0+ serial wire) and boot in RAM selection disabled (debugline fuse)

The firewall protects parts of code/data from access by the rest of the code that is executed outside of the protected area. The granularity of the protected code segment or the non-volatile data segment is 256 bytes (Flash memory or EEPROM) against 64 bytes for the volatile data segment (RAM).

The whole non-volatile memory embeds the error correction code (ECC) feature.

3.9 Boot modes

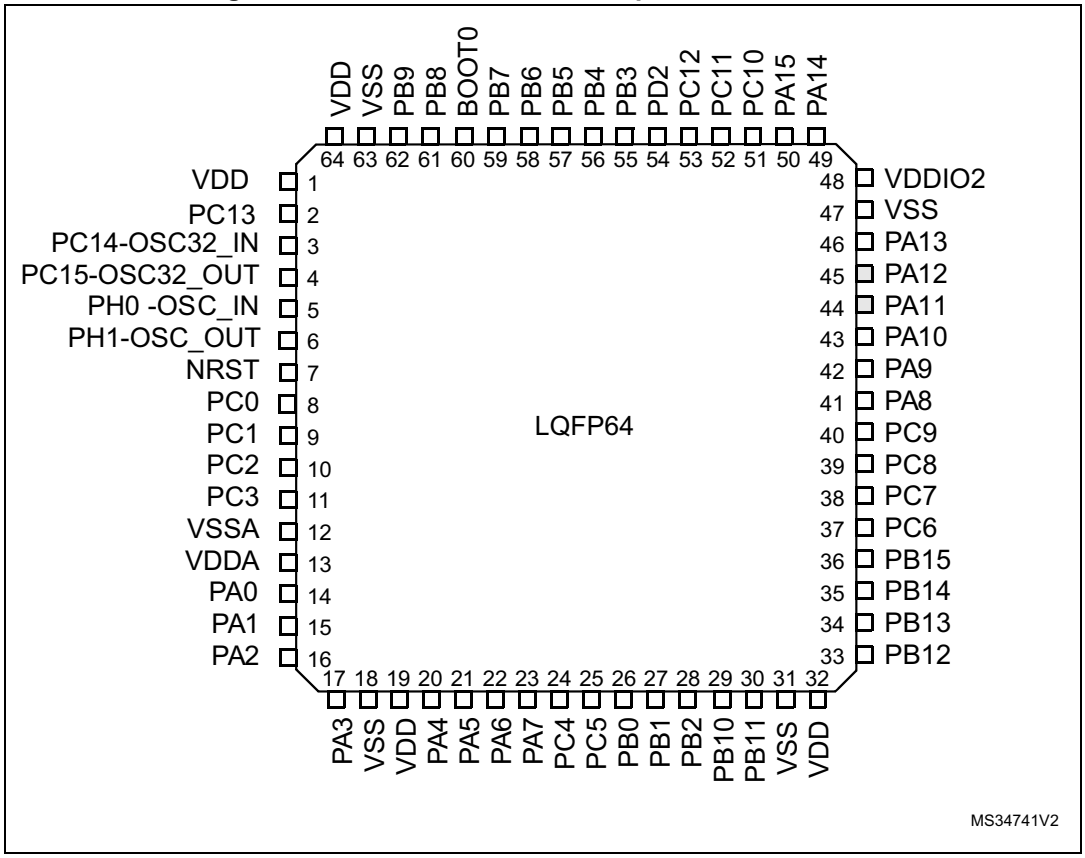
At startup, BOOT0 pin and nBOOT1 option bit are used to select one of three boot options:

- Boot from Flash memory
- Boot from System memory
- Boot from embedded RAM

The boot loader is located in System memory. It is used to reprogram the Flash memory by using SPI1(PA4, PA5, PA6, PA7) or SPI2 (PB12, PB13, PB14, PB15), USART1(PA9, PA10) or USART2(PA2, PA3). See STM32™ microcontroller system memory boot mode AN2606 for details.

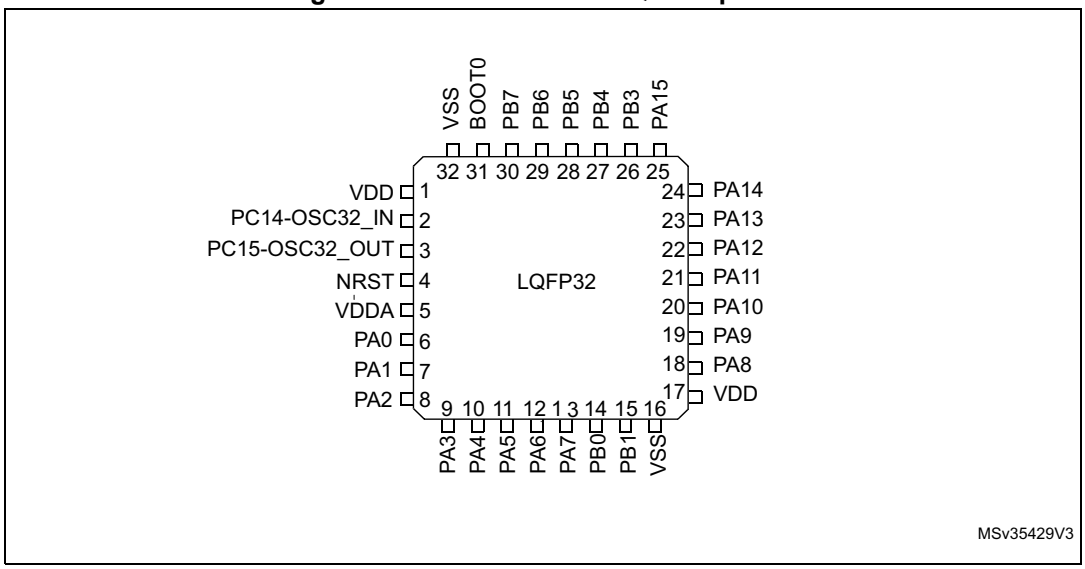
4 Pin descriptions

Figure 3. STM32L051x6/8 LQFP64 pinout - 10 x 10 mm



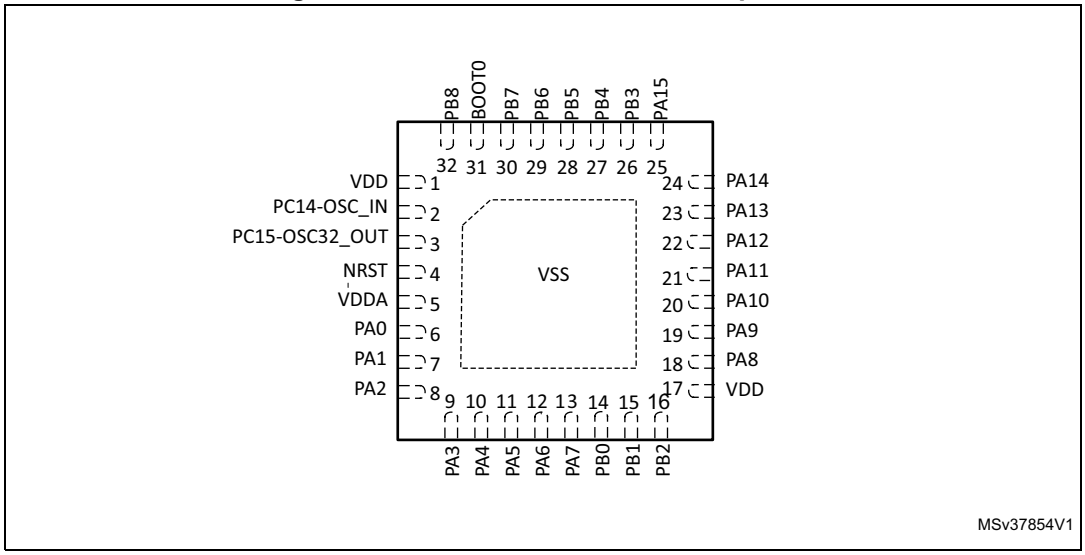
1. The above figure shows the package top view.
2. I/O supplied by VDDIO2.

Figure 7. STM32L051x6/8 LQFP32 pinout



1. The above figure shows the package top view.

Figure 8. STM32L051x6/8 UFQFPN32 pinout



1. The above figure shows the package top view.

Table 15. STM32L051x6/8 pin definitions (continued)

Pin Number						Pin name (function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
LQFP64	TFBGA64	LQFP48	WLCSP36[1]	LQFP32	UFQFPN32						
5	C1	5	-	-	-	PH0-OSC_IN (PH0)	I/O	TC	-	-	OSC_IN
6	D1	6	-	-	-	PH1-OSC_OUT (PH1)	I/O	TC	-	-	OSC_OUT
7	E1	7	C6	4	4	NRST	I/O	RST	-	-	-
8	E3	-	-	-	-	PC0	I/O	FT	-	LPTIM1_IN1, EVENTOUT	ADC_IN10
9	E2	-	-	-	-	PC1	I/O	FT	-	LPTIM1_OUT, EVENTOUT	ADC_IN11
10	F2	-	-	-	-	PC2	I/O	FT	-	LPTIM1_IN2, SPI2_MISO/I2S2_MCK	ADC_IN12
11	-	-	-	-	-	PC3	I/O	FT	-	LPTIM1_ETR, SPI2_MOSI/I2S2_SD	ADC_IN13
12	F1	8	-	-	-	VSSA	S		-	-	-
-	G1	-	E6	-	-	VREF+	S		-	-	-
13	H1	9	D5	5	5	VDDA	S		-	-	-
14	G2	10	D4	6	6	PA0	I/O	TC	-	TIM2_CH1, USART2_CTS, TIM2_ETR, COMP1_OUT	COMP1_INM6, ADC_IN0, RTC_TAMP2/WKUP1
15	H2	11	F6	7	7	PA1	I/O	FT	-	EVENTOUT, TIM2_CH2, USART2_RTS_DE, TIM21_ETR	COMP1_INP, ADC_IN1
16	F3	12	E5	8	8	PA2	I/O	FT	-	TIM21_CH1, TIM2_CH3, USART2_TX, COMP2_OUT	COMP2_INM6, ADC_IN2
17	G3	13	F5	9	9	PA3	I/O	FT	-	TIM21_CH2, TIM2_CH4, USART2_RX	COMP2_INP, ADC_IN3
18	C2	-	-	-	-	VSS	S		-	-	-

Table 15. STM32L051x6/8 pin definitions (continued)

Pin Number						Pin name (function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
LQFP64	TFBGA64	LQFP48	WLCSP36[1]	LQFP32	UFQFPN32						
19	D2	-	-	-	-	VDD	S		-	-	-
20	H3	14	E4	10	10	PA4	I/O	TC		SPI1_NSS, USART2_CK, TIM22_ETR	COMP1_INM4, COMP2_INM4, ADC_IN4
21	F4	15	F4	11	11	PA5	I/O	TC	-	SPI1_SCK, TIM2_ETR, TIM2_CH1	COMP1_INM5, COMP2_INM5, ADC_IN5
22	G4	16	E3	12	12	PA6	I/O	FT	-	SPI1_MISO, LPUART1_CTS, TIM22_CH1, EVENTOUT, COMP1_OUT	ADC_IN6
23	H4	17	F3	13	13	PA7	I/O	FT	-	SPI1_MOSI, TIM22_CH2, EVENTOUT, COMP2_OUT	ADC_IN7
24	H5	-	-	-	-	PC4	I/O	FT	-	EVENTOUT, LPUART1_TX	ADC_IN14
25	H6	-	-	-	-	PC5	I/O	FT	-	LPUART1_RX,	ADC_IN15
26	F5	18	D3	14	14	PB0	I/O	FT	-	EVENTOUT	ADC_IN8, VREF_OUT
27	G5	19	C3	15	15	PB1	I/O	FT	-	LPUART1_RTS_DE	ADC_IN9, VREF_OUT
28	G6	20	F2	-	16	PB2	I/O	FT	-	LPTIM1_OUT	-
29	G7	21	E2	-	-	PB10	I/O	FT	-	TIM2_CH3, LPUART1_TX, SPI2_SCK, I2C2_SCL	-
30	H7	22	D2	-	-	PB11	I/O	FT	-	EVENTOUT, TIM2_CH4, LPUART1_RX, I2C2_SDA	-
31	D6	23	-	16	-	VSS	S	-	-	-	-
32	E6	24	F1	17	17	VDD	S	-	-	-	-

Table 15. STM32L051x6/8 pin definitions (continued)

Pin Number						Pin name (function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
LQFP64	TFBGA64	LQFP48	WLCSP36[1]	LQFP32	UFQFPN32						
63	D4	47	D6	32	-	VSS	S	-	-	-	-
64	E4	48	A5	1	1	VDD	S	-	-	-	-

1. PB9/12/13/14/15, PH0/1 and PC13 GPIOs should be configured as output and driven Low, even if they are not available on this package.

Table 31. Current consumption in Sleep mode

Symbol	Parameter	Conditions		f_{HCLK}	Typ	Max(1)	Unit
I_{DD} (Sleep)	Supply current in Sleep mode, Flash OFF	f_{HSE} = f_{HCLK} up to 16 MHz included, f_{HSE} = f_{HCLK}/2 above 16 MHz (PLL ON)(2)	Range 3, V_{CORE}=1.2 V, VOS[1:0]=11	1 MHz	43.5	90	µA
				2 MHz	72	120	
				4 MHz	130	180	
			Range 2, V_{CORE}=1.5 V, VOS[1:0]=10	4 MHz	160	210	
				8 MHz	305	370	
				16 MHz	590	710	
			Range 1, V_{CORE}=1.8 V, VOS[1:0]=01	8 MHz	370	430	
				16 MHz	715	860	
				32 MHz	1650	1900	
		MSI clock	Range 3, V_{CORE}=1.2 V, VOS[1:0]=11	65 kHz	18	65	
				524 kHz	31.5	75	
				4.2 MHz	140	210	
		HSI16 clock source (16 MHz)	Range 2, V_{CORE}=1.5 V, VOS[1:0]=10	16 MHz	665	830	
			Range 1, V_{CORE}=1.8 V, VOS[1:0]=01	32 MHz	1750	2100	
	Supply current in Sleep mode, Flash ON	f_{HSE} = f_{HCLK} up to 16 MHz included, f_{HSE} = f_{HCLK}/2 above 16 MHz (PLL ON)(2)	Range 3, V_{CORE}=1.2 V, VOS[1:0]=11	1 MHz	57.5	130	
				2 MHz	84	170	
				4 MHz	150	280	
			Range 2, CORE=1.5 V, VOS[1:0]=10	4 MHz	170	310	
				8 MHz	315	420	
				16 MHz	605	770	
			Range 1, V_{CORE}=1.8 V, VOS[1:0]=01	8 MHz	380	460	
				16 MHz	730	950	
				32 MHz	1650	2400	
		MSI clock	Range 3, V_{CORE}=1.2 V, VOS[1:0]=11	65 kHz	29.5	110	
				524 kHz	44.5	130	
				4.2 MHz	150	270	
		HSI16 clock source (16 MHz)	Range 2, V_{CORE}=1.5 V, VOS[1:0]=10	16 MHz	680	950	
			Range 1, V_{CORE}=1.8 V, VOS[1:0]=01	32 MHz	1750	2100	

1. Guaranteed by characterization results at 125 °C, unless otherwise specified.

6.3.6 External clock source characteristics

High-speed external user clock generated from an external source

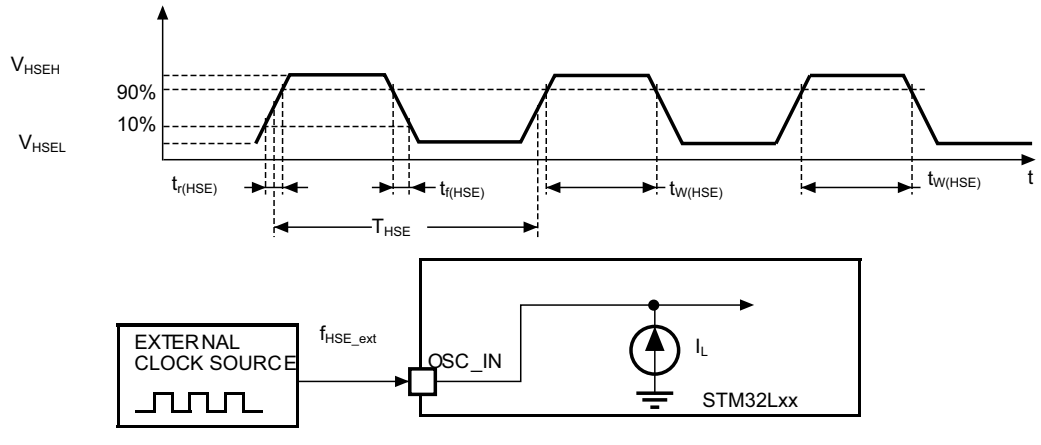
In bypass mode the HSE oscillator is switched off and the input pin is a standard GPIO.The external clock signal has to respect the I/O characteristics in *Section 6.3.12*. However, the recommended clock input waveform is shown in *Figure 19*.

Table 40. High-speed external user clock characteristics(1)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{HSE_ext}	User external clock source frequency	CSS is ON or PLL is used	1	8	32	MHz
		CSS is OFF, PLL not used	0	8	32	MHz
V_{HSEH}	OSC_IN input pin high level voltage	-	$0.7V_{DD}$	-	V_{DD}	V
V_{HSEL}	OSC_IN input pin low level voltage		V_{SS}	-	$0.3V_{DD}$	
$t_{w(HSE)}$ $t_{w(HSE)}$	OSC_IN high or low time		12	-	-	ns
$t_{r(HSE)}$ $t_{f(HSE)}$	OSC_IN rise or fall time		-	-	20	
$C_{in(HSE)}$	OSC_IN input capacitance		-	2.6	-	pF
$DuCy_{(HSE)}$	Duty cycle		45	-	55	%
I_L	OSC_IN Input leakage current	$V_{SS} \leq V_{IN} \leq V_{DD}$	-	-	±1	µA

1. Guaranteed by design.

Figure 19. High-speed external clock source AC timing diagram



6.3.12 I/O current injection characteristics

As a general rule, current injection to the I/O pins, due to external voltage below V_{SS} or above V_{DD} (for standard pins) should be avoided during normal product operation. However, in order to give an indication of the robustness of the microcontroller in cases when abnormal injection accidentally happens, susceptibility tests are performed on a sample basis during device characterization.

Functional susceptibility to I/O current injection

While a simple application is executed on the device, the device is stressed by injecting current into the I/O pins programmed in floating input mode. While current is injected into the I/O pin, one at a time, the device is checked for functional failures.

The failure is indicated by an out of range parameter: ADC error above a certain limit (higher than 5 LSB TUE), out of conventional limits of induced leakage current on adjacent pins (out of –5 µA/+0 µA range), or other functional failure (for example reset occurrence oscillator frequency deviation).

The test results are given in the *Table 55*.

Table 55. I/O current injection susceptibility

Symbol	Description	Functional susceptibility		Unit
		Negative injection	Positive injection	
I_{INJ}	Injected current on BOOT0	-0	NA	mA
	Injected current on PA0, PA4, PA5, PA11, PA12, PC15, PH0 and PH1	-5	0	
	Injected current on any other FT, FTf pins	-5 (1)	NA	
	Injected current on any other pins	-5 (1)	+5	

1. It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative currents.

Output voltage levels

Unless otherwise specified, the parameters given in *Table 57* are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in *Table 23*. All I/Os are CMOS and TTL compliant.

Table 57. Output voltage characteristics

Symbol	Parameter	Conditions	Min	Max	Unit
V_{OL} (1)	Output low level voltage for an I/O pin	CMOS port(2), I_{IO} = +8 mA 2.7 V ≤ V_{DD} ≤ 3.6 V	-	0.4	V
V_{OH} (3)	Output high level voltage for an I/O pin		V_{DD}-0.4	-	
V_{OL} (1)	Output low level voltage for an I/O pin	TTL port(2), I_{IO} =+ 8 mA 2.7 V ≤V_{DD} ≤ 3.6 V	-	0.4	
V_{OH} (3)(4)	Output high level voltage for an I/O pin	TTL port(2), I_{IO} = -6 mA 2.7 V ≤V_{DD} ≤ 3.6 V	2.4	-	
V_{OL} (1)(4)	Output low level voltage for an I/O pin	I_{IO} = +15 mA 2.7 V ≤V_{DD} ≤ 3.6 V	-	1.3	
V_{OH} (3)(4)	Output high level voltage for an I/O pin	I_{IO} = -15 mA 2.7 V ≤V_{DD} ≤ 3.6 V	V_{DD}-1.3	-	
V_{OL} (1)(4)	Output low level voltage for an I/O pin	I_{IO} = +4 mA 1.65 V ≤V_{DD} < 3.6 V	-	0.45	
V_{OH} (3)(4)	Output high level voltage for an I/O pin	I_{IO} = -4 mA 1.65 V ≤V_{DD} ≤ 3.6 V	V_{DD}-0.45	-	
V_{OLFM+} (1)(4)	Output low level voltage for an FTf I/O pin in Fm+ mode	I_{IO} = 20 mA 2.7 V ≤V_{DD} ≤ 3.6 V	-	0.4	
		I_{IO} = 10 mA 1.65 V ≤V_{DD} ≤ 3.6 V	-	0.4	

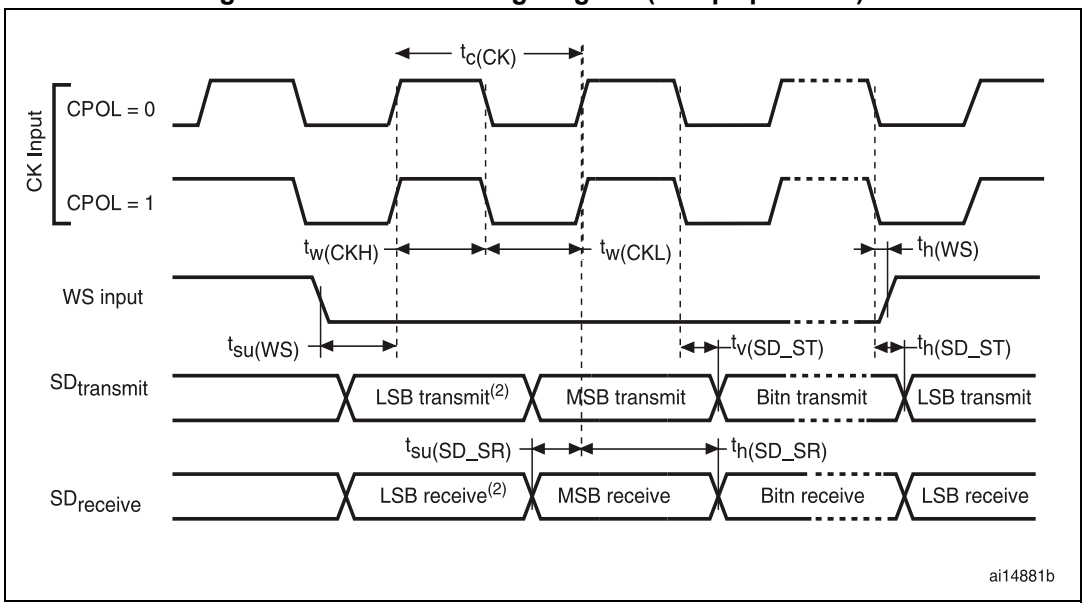
1. The I_{IO} current sunk by the device must always respect the absolute maximum rating specified in *Table 21*. The sum of the currents sunk by all the I/Os (I/O ports and control pins) must always be respected and must not exceed $\Sigma I_{IO(PIN)}$.
2. TTL and CMOS outputs are compatible with JEDEC standards JESD36 and JESD52.
3. The I_{IO} current sourced by the device must always respect the absolute maximum rating specified in *Table 21*. The sum of the currents sourced by all the I/Os (I/O ports and control pins) must always be respected and must not exceed $\Sigma I_{IO(PIN)}$.
4. Guaranteed by characterization results.

Table 60. ADC characteristics (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
R_{AIN}(3)	External input impedance	See *Equation 1* and *Table 61* for details	-	-	50	kΩ
R_{ADC}(3)(4)	Sampling switch resistance	-	-	-	1	kΩ
C_{ADC}(3)	Internal sample and hold capacitor	-	-	-	8	pF
t_{CAL}(3)(5)	Calibration time	f_{ADC} = 16 MHz	5.2			µs
		-	83			$1/f_{ADC}$
$W_{LATENCY}$(6)	ADC_DR register write latency	ADC clock = HSI16	1.5 ADC cycles + 2 f_{PCLK} cycles	-	1.5 ADC cycles + 3 f_{PCLK} cycles	-
		ADC clock = PCLK/2	-	4.5	-	f_{PCLK} cycle
		ADC clock = PCLK/4	-	8.5	-	f_{PCLK} cycle
t_{latr}(3)	Trigger conversion latency	$f_{ADC} = f_{PCLK}/2$ = 16 MHz	0.266			µs
		$f_{ADC} = f_{PCLK}/2$	8.5			$1/f_{PCLK}$
		$f_{ADC} = f_{PCLK}/4$ = 8 MHz	0.516			µs
		$f_{ADC} = f_{PCLK}/4$	16.5			$1/f_{PCLK}$
		$f_{ADC} = f_{HSI16}$ = 16 MHz	0.252	-	0.260	µs
$Jitter_{ADC}$	ADC jitter on trigger conversion	$f_{ADC} = f_{HSI16}$	-	1	-	$1/f_{HSI16}$
t_S(3)	Sampling time	f_{ADC} = 16 MHz	0.093	-	10.03	µs
		-	1.5	-	160.5	$1/f_{ADC}$
t_{UP_LDO}(3)(5)	Internal LDO power-up time	-	-	-	10	µs
t_{STAB}(3)(5)	ADC stabilization time	-	14			$1/f_{ADC}$
t_{ConV}(3)	Total conversion time (including sampling time)	f_{ADC} = 16 MHz, 12-bit resolution	0.875	-	10.81	µs
		12-bit resolution	14 to 173 (t_S for sampling +12.5 for successive approximation)			$1/f_{ADC}$

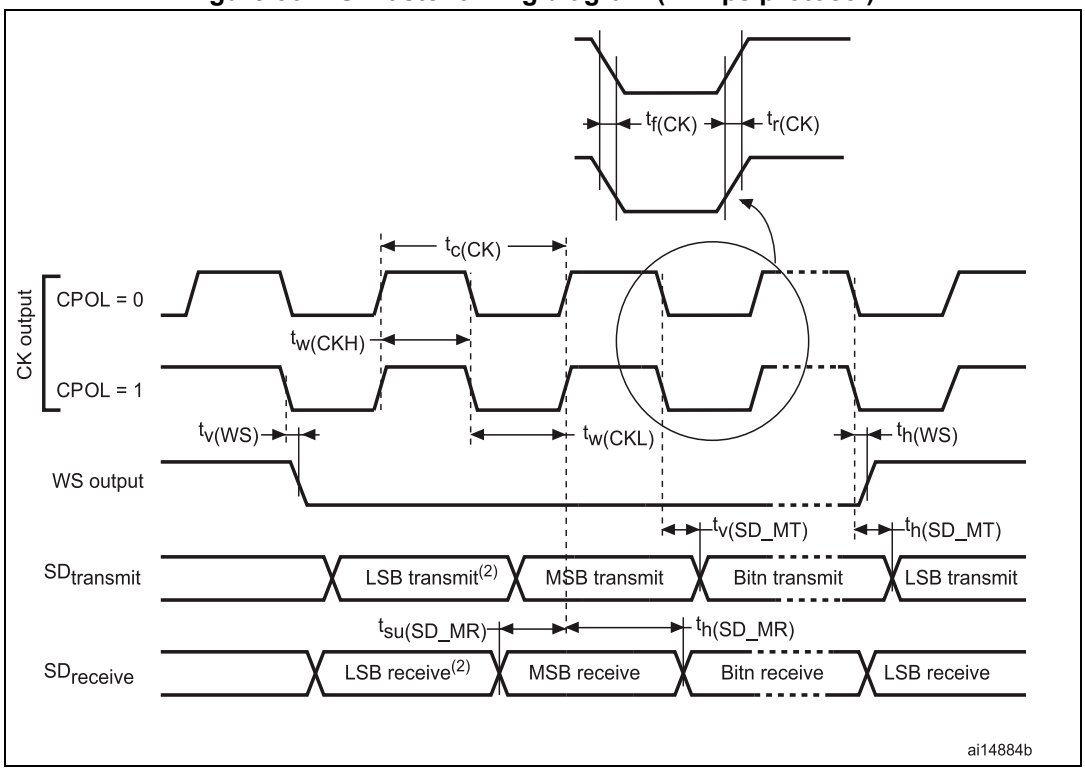
1. V_{DDA} minimum value can be decreased in specific temperature conditions. Refer to *Table 61: RAIN max for fADC = 16 MHz*.
2. A current consumption proportional to the APB clock frequency has to be added (see *Table 37: Peripheral current consumption in Run or Sleep mode*).
3. Guaranteed by design.
4. Standard channels have an extra protection resistance which depends on supply voltage. Refer to *Table 61: RAIN max for fADC = 16 MHz*.
5. This parameter only includes the ADC timing. It does not take into account register access latency.
6. This parameter specifies the latency to transfer the conversion result into the ADC_DR register. EOC bit is set to indicate the conversion is complete and has the same latency.

Figure 35. I²S slave timing diagram (Philips protocol)(1)



1. Measurement points are done at CMOS levels: $0.3 \times V_{DD}$ and $0.7 \times V_{DD}$.
2. LSB transmit/receive of the previously transmitted byte. No LSB transmit/receive is sent before the first byte.

Figure 36. I²S master timing diagram (Philips protocol)(1)



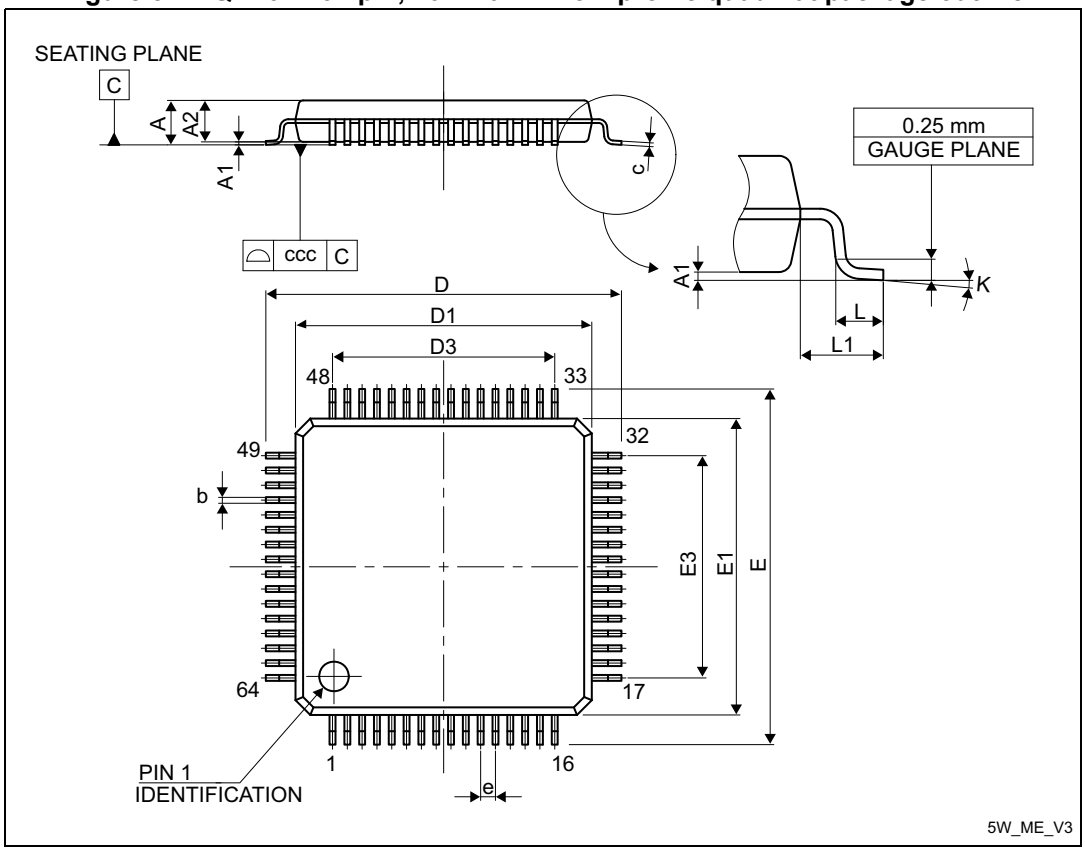
1. Guaranteed by characterization results.
2. LSB transmit/receive of the previously transmitted byte. No LSB transmit/receive is sent before the first byte.

7 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status *are available at www.st.com.* ECOPACK® is an ST trademark.

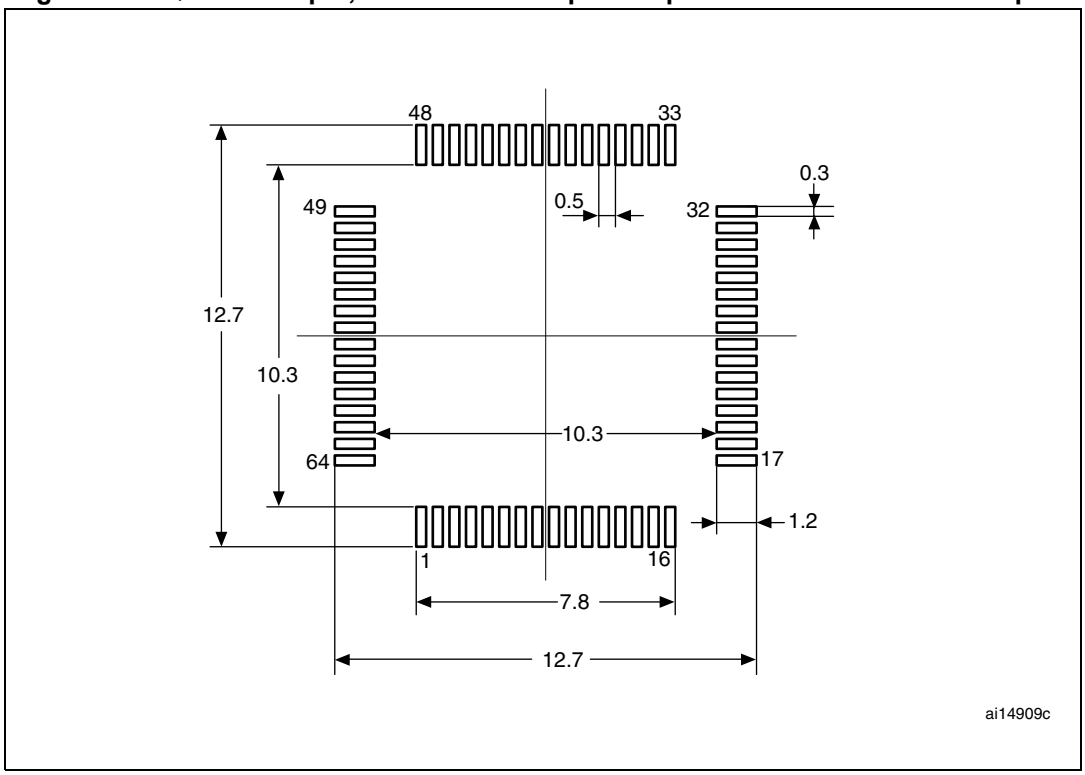
7.1 LQFP64 package information

Figure 37. LQFP64 - 64-pin, 10 x 10 mm low-profile quad flat package outline



1. Drawing is not to scale.

Figure 38. LQFP64 - 64-pin, 10 x 10 mm low-profile quad flat recommended footprint



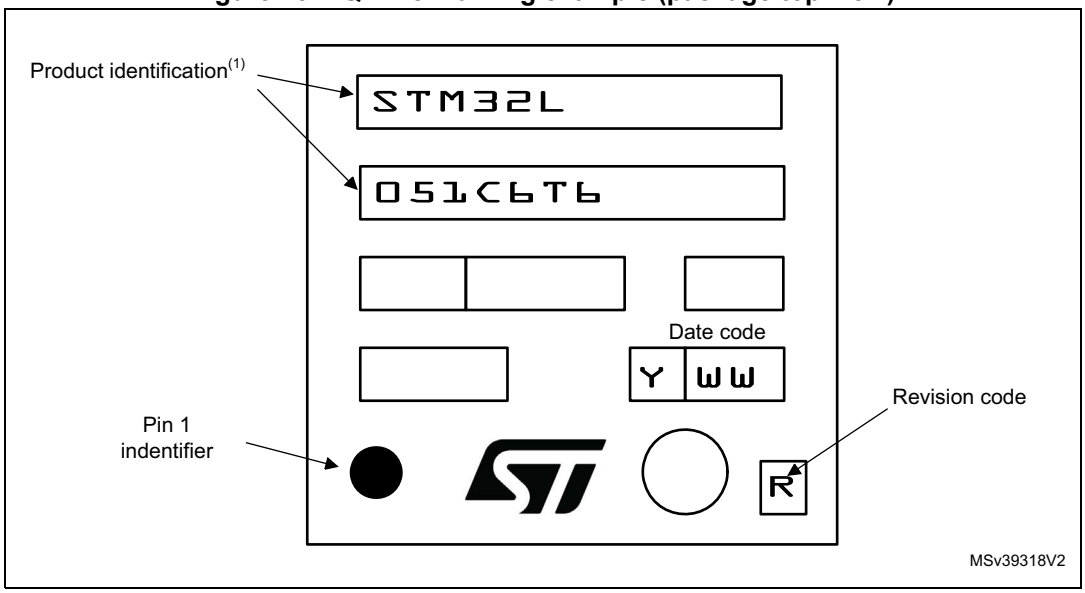
1. Dimensions are expressed in millimeters.

Device marking for LQFP48

The following figure gives an example of topside marking versus pin 1 position identifier location.

Other optional marking or inset/upset marks, which depend on supply chain operations, are not indicated below.

Figure 45. LQFP48 marking example (package top view)



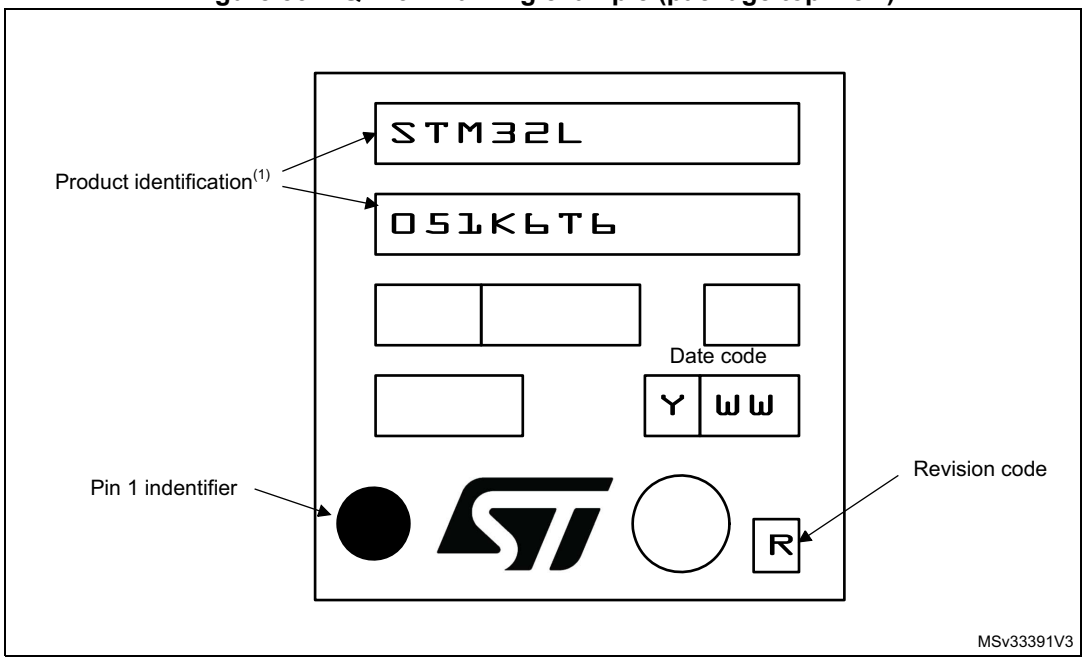
1. Parts marked as “ES”, “E” or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.

Device marking for LQFP32

The following figure gives an example of topside marking versus pin 1 position identifier location.

Other optional marking or inset/upset marks, which depend on supply chain operations, are not indicated below.

Figure 53. LQFP32 marking example (package top view)



1. Parts marked as “ES”, “E” or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.

Table 86. Document revision history (continued)

Date	Revision	Changes
25-Jun-2014	3	Cover page: changed LQFP32 size, updated core speed. updated core speed, added minimum supply voltage for ADC and comparators. ADC now guaranteed down to 1.65 V. Updated list of applications in *Section 1: Introduction*. Changed number of I2S interfaces to one in *Section 2: Description*. Updated *Table 2: Ultra-low-power STM32L051x6/x8 device features and peripheral counts*. Updated *Table 3: Functionalities depending on the operating power supply range*. Updated RTC/TIM21 in *Table 6: STM32L0xx peripherals interconnect matrix*. Added note related to UFQFPN32 and note related to WLCSP36 in *Table 15: STM32L051x6/8 pin definitions*. Split LQFP32/UFQFPN32 pinout schematics into two distinct figures: *Figure 7* and *Figure 8*. Updated V_{DDA} in *Table 23: General operating conditions*. Split Table *Current consumption in Run mode, code with data processing running from Flash* into *Table 27* and *Table 28* and content updated. Split Table *Current consumption in Run mode, code with data processing running from RAM* into *Table 29* and *Table 30* and content updated. Updated *Table 31: Current consumption in Sleep mode*, *Table 32: Current consumption in Low-power run mode*, *Table 33: Current consumption in Low-power sleep mode*, *Table 34: Typical and maximum current consumptions in Stop mode*, *Table 35: Typical and maximum current consumptions in Standby mode*, and added *Table 36: Average current consumption during Wakeup*. Updated *Table 37: Peripheral current consumption in Run or Sleep mode* and added *Table 38: Peripheral current consumption in Stop and Standby mode*. Updated t_{LOCK} in *Table 47: PLL characteristics*. Removed note 1 below *Figure 21: HSE oscillator circuit diagram*. Updated *Table 49: Flash memory and data EEPROM characteristics* and *Table 50: Flash memory and data EEPROM endurance and retention*. Updated *Table 58: I/O AC characteristics*. Updated *Table 60: ADC characteristics*. Updated *Figure 57: Thermal resistance* and added note 1.

Table 86. Document revision history (continued)

Date	Revision	Changes
17-Mar-2016	6	Updated number of SPIs on cover page and in *Table 2: Ultra-low-power STM32L051x6/x8 device features and peripheral counts*. Changed minimum comparator supply voltage to 1.65 V on cover page. Added number of fast and standard channels in *Section 3.11: Analog-to-digital converter (ADC)*. Updated *Section 3.16.2: Universal synchronous/asynchronous receiver transmitter (USART)* and *Section 3.16.4: Serial peripheral interface (SPI)/Inter-integrated sound (I2S)* to mention the fact that USARTs with synchronous mode feature can be used as SPI master interfaces. Added baudrate allowing to wake up the MCU from Stop mode in *Section 3.16.2: Universal synchronous/asynchronous receiver transmitter (USART)* and *Section 3.16.3: Low-power universal asynchronous receiver transmitter (LPUART)*. In *Section 6: Electrical characteristics*, updated notes related to values guaranteed by characterization. Changed V_{DDA} minimum value to 1.65 V in *Table 23: General operating conditions*. *Section 6.3.15: 12-bit ADC characteristics*: – *Table 60: ADC characteristics*: Distinction made between V_{DDA} for fast and standard channels; added note *1.* Added note 4 related to R_{ADC}. Updated f_{TRIG} and V_{AIN} maximum value. Updated t_S and t_{CONV}. Added V_{REF+}. – Updated equation 1 description. – Updated *Table 61: RAIN max for fADC = 16 MHz* for f_{ADC} = 16 MHz and distinction made between fast and standard channels. Added *Table 69: USART/LPUART characteristics*. Updated *Figure 45: LQFP48 marking example (package top view)*.

Table 86. Document revision history (continued)

Date	Revision	Changes
07-Mar-2017	7	Added thin WLCSP36 package Updated number of I2S interfaces in *Table 2: Ultra-low-power STM32L051x6/x8 device features and peripheral counts*. Removed note 2 related to PA4 in *Table 15: STM32L051x6/8 pin definitions* Added mission profile compliance with JEDEC JESD47 in *Section 6.2: Absolute maximum ratings*. Removed CRS from *Table 37: Peripheral current consumption in Run or Sleep mode*. Added note 2. related to the position of the external capacitor below *Figure 27: Recommended NRST pin protection*. Updated R_L in *Table 60: ADC characteristics*. Updated t_{AF} maximum value for range 1 in *Table 68: I2C analog filter characteristics*. Updated $t_{WUUSART}$ description in *Table 69: USART/LPUART characteristics*. NSS timing waveforms updated in *Figure 32: SPI timing diagram - slave mode and CPHA = 0* and *Figure 33: SPI timing diagram - slave mode and CPHA = 1(1)*. Added reference to optional marking or inset/upset marks in all package device marking sections. Previous WLCSP36 package renamed “Standard” WLCSP36; added Note *2.* below *Figure 46: Standard WLCSP36 - 2.61 x 2.88 mm, 0.4 mm pitch wafer level chip scale package outline* and updated *Table 78: Standard WLCSP36 - 2.61 x 2.88 mm, 0.4 mm pitch wafer level chip scale mechanical data*.